



MBE - Material Division

The Material Division operates a multi-chamber facility for the fabrication of compound semiconductors by **means of molecular beam epitaxy** (MBE).

The facility includes two interconnected Riber 32P MBE chambers for the growth of III-V and II-V semiconductors, an analysis chamber with a monochromatic x-ray photoemission spectroscopy (XPS) facility and a metallization chamber.

Structures fabricated by the Division are currently based on GaAs, AlAs, InAs, CdTe, ZnSe, CdSe, MgSe, and ZnS semiconductors and the related ternary and quaternary alloys.

Ongoing programs focus on new materials for optoelectronics and spintronics, quantum-confined structures, quantum dots and nanowires.

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